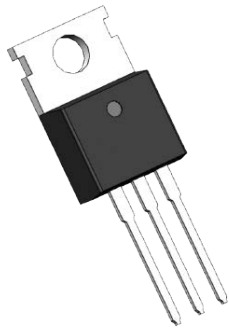
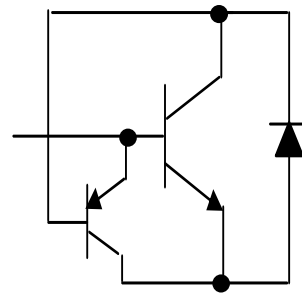


Features:

- 特点: ■击穿的电压稳定■开关速度快■安全工作区宽■符合ROHS规范
- FEATURES:■HIGH VOLTAGE CAPABILITY ■HIGH SPEED SWITCHING ■WIDE SOA ■ROHS COMPLIANT
- 应用■节能灯■电子镇流器■电子变压器等开关电路
- APPLICATION:■FLUORESCENT LAMP ■ELECTRONIC BALLAST ■ELECTRONIC TRANSFORMER ECT.



Marking and pin assignment



封装形式: TO-220 BCE

●Absolute Maximum Ratings (Tc=25°C)

参数名称 PARAMETER	符号 SYMBOL	额定值 VALUE	单位 UNIT
集电极 基极电压Collector-Base Voltage	VCBO	600	V
集电极 发射极电压Collector-Emitter Voltage	VCEO	410	V
发射极 基极Emitter-Base Voltage	VEBO	9	V
集电极电流 Collector Current	Ic	1.8	A
集电极耗散功率 Total Power Dissipation	PC	38	W
最高工作温度 Junction Temperature	Tj	150	°C
贮存温度 Storage Temperature	TsTg	-55-150	°C

Package Marking and Ordering Information

Part NO.	Marking	Package
MJE13003	E13003	TO-220

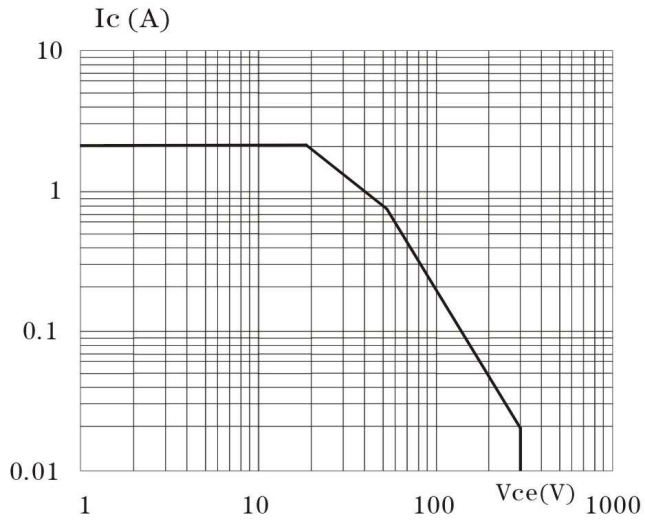
Electrical Characteristics (Tc=25°C)

参数名称 CHARACTERISTICS	符号 SYMBOL	测试条件 TEST CONDITION	最小值 MIN	最大值 MAX	单位 UNIT
集电极-基极截止电流 Collector-Base Cutoff Current	ICBO	VCB=600V		5	uA
集电极-发射极截止电流 Collector-Emitter Cutoff Current	ICEO	VCE=400V, IB=0		10	uA
集电极-发射极电压 Collector-Emitter Voltage	VCEO	IC=10mA, IB=0	410		V
发射极-基极电压 Collector-Base Voltage	VEBO	IE=1mA, IC=0	9		V
集电极-发射极饱和压降 Collector-Emitter Saturation Voltage	Vcesat	IC=500mA, IB=100mA		0.3	
		IC=1.0A, IB=0.2A		0.55	V
		IC=1.5A, IB=0.5A		0.85	V
发射极-基极饱和压降 Base-Emitter Saturation Voltage	Vbesat	IC=1.5A, IB=500mA		1.2	V
电流放大倍数 DC Current Gain	Hfe	VCE=5V, IC=200uA	8		
		VCE=5V, IC=250mA	15	30	
		VCE=5V, IC=1.5A	6		
贮存时间 Storage Time	ts	VCC=5V IC=0.25A (UI9600)	1.5	3.0	us
下降时间 falling time	tf			0.8	

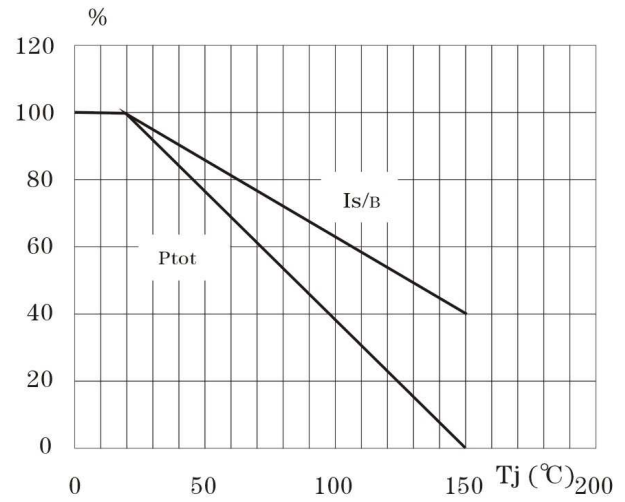
注意事项： 1、使用时不要外接续流保护二极管

2、基极驱动电流应较强，确保不出现基极驱动不足，但也不能太强，超过 PNP管的控制范围。

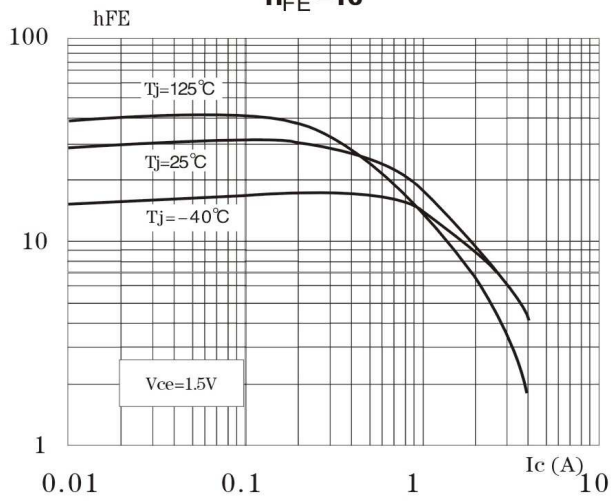
SOA(DC)



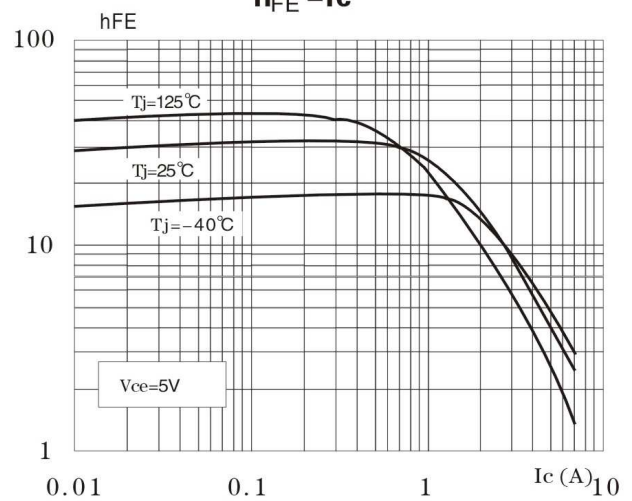
$P_c \propto T_j$



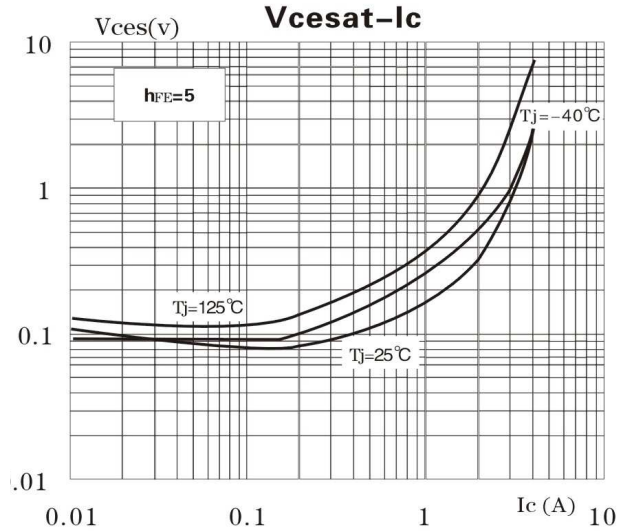
$h_{FE} - I_c$



$h_{FE} - I_c$



$V_{cesat} - I_c$



$V_{besat} - I_c$

